

N-CHANNEL ENHANCEMENT MODE MOSFET

DMG9N65CT

Product Summary

BV _{DSS}	Rds(on) max	Package	I _{D MAX} T _C = +25°С
650V	$1.3\Omega @ V_{GS} = 10V$	TO220AB	9.0A

Description

This new generation complementary dual MOSFET features low onresistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

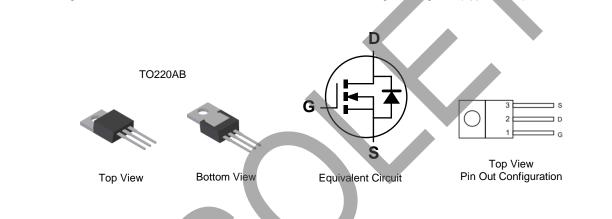
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



Ordering Information (Note 4)

DMG9N65CT TO220AB 50 Pieces/Tube	Part Number	Case	Packaging
	DMG9N65CT	TO220AB	

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

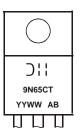
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

TO220AB



) ! != Manufacturer's Marking
9N65CT = Product Type Marking Code
AB = Foundry and Assembly Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic				Value	Unit
Drain-Source Voltage			VDSS	650	V
Gate-Source Voltage			V _{GSS}	±30	V
Steady $T_c = +25^{\circ}C$				9.0	٨
Continuous Drain Current (Note 5) $V_{GS} = 10V$	T _C = +70°C	ID	7.0	A	
Pulsed Drain Current (Note 6) 10µs Pulse, Pulse Duty Cycle<=1%			IDМ	30	A
Avalanche Current (Note 7) V_{DD} = 100V, V_{GS} = 10V, L = 60mH			I _{AR}	2.7	A
Repetitive Avalanche Energy (Note 7) V_{DD} = 100V, V_{GS} = 10V, L = 60mH			E _{AR}	260	mJ

Thermal Characteristics

Cł	aracteristic	Symbol		Max		Unit
	$T_{C} = +25^{\circ}C$	_		165		
Power Dissipation (Note 5)	T _C = +70°C	PD		100		W
Thermal Resistance, Junction to	Case (Note 5)	Rejc		0.7		°C/W
Operating and Storage Temperature Range		TJ, TSTG		-55 to +150		°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BVDSS	650		_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—		1.0	μA	$V_{DS} = 650V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	—	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	3	—	5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	RDS(ON)	_	0.7	1.3	Ω	$V_{GS} = 10V, I_D = 4.5A$
Forward Transfer Admittance	Y _{fs}	Ι	8.5	_	s	$V_{DS} = 40V, I_D = 4.5A$
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	2,310	-		
Output Capacitance	C _{oss}	_	122	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.2			
Gate Resistance	Rg		2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg		39	-		
Gate-Source Charge	Q _{gs}		8.5	_	nC	V _{GS} = 10V, V _{DS} = 520V, I _D = 8A
Gate-Drain Charge	Q_gd		11.9	_		ID = OA
Turn-On Delay Time	t _{D(ON)}		39		ns	
Turn-On Rise Time	t _R		29	_	ns	$V_{GS} = 10V, V_{DS} = 325V,$
Turn-Off Delay Time	t _{D(OFF)}		122		ns	$R_g = 25\Omega, I_D = 8A$
Turn-Off Fall Time	t _F		28	_	ns	
Body Diode Reverse Recovery Time	t _{RR}	_	570	_	ns	dl/dt = 100A/µs, V _{DS} = 100V,
Body Diode Reverse Recovery Charge	Q _{RR}		4.17	_	μC	I _F = 8A

Notes: 5. Device mounted on an infinite heatsink.

6. Repetitive rating, pulse width limited by junction temperature.

7. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

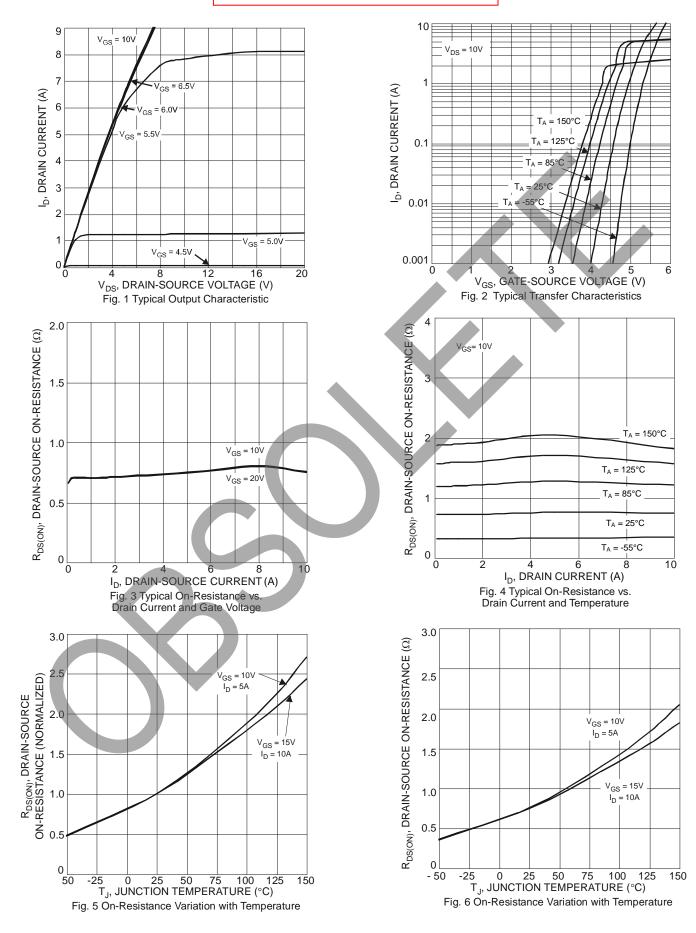
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.



PART OBSOLETE - Use DMG7N65SCT

DMG9N65CT



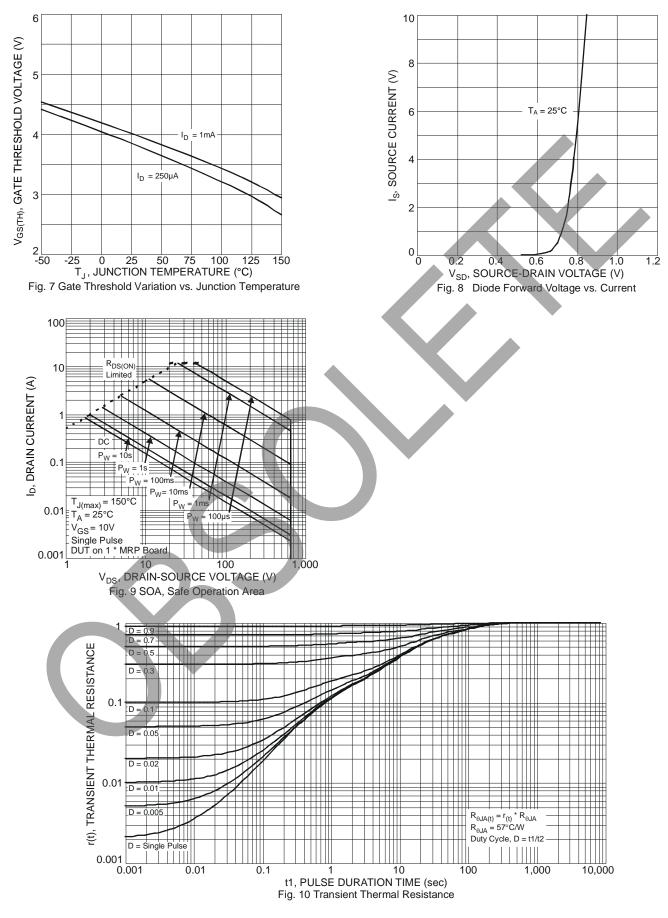
OBSOLETE - PART DISCONTINUED

DMG9N65CT Document number: DS35619 Rev. 10 - 4



PART OBSOLETE - Use DMG7N65SCT

DMG9N65CT

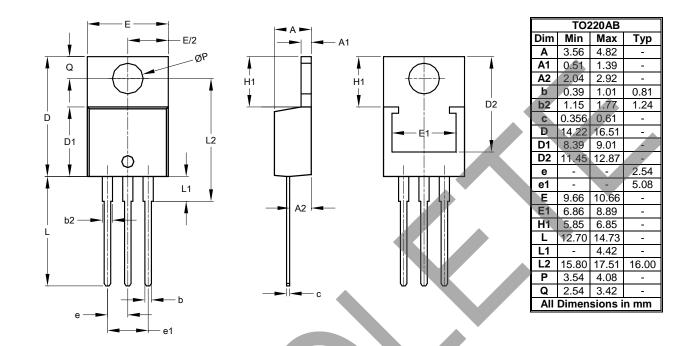




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance.





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